

Appendix 1

Table S1. Selected crystallographic parameters from structure solution (SIR2014) and dynamical refinement (JAAN2006) of wenjiite.

Crystallographic information	
Cell content	$P_{1.6}Si_{5.4}Ti_{10}$
Space group	$P6_3/mcm$
a (Å)	7.30(10)
c (Å)	5.09(10)
Volume (Å ³)	235(6)
Structure solution parameters	
Data resolution (Å)	0.9
No. of sampled reflections	625
No. of independent reflections	67
Independent reflections coverage (%)	94
Global thermal factor U_{iso} (Å ²)	0.005
$R_{int}(F)$ (%)	21.51
$R_{sir}(F)$ (%)	23.58
Dynamical structure refinement parameters	
No. of zones used for refinement	93
No. of reflections (all)	1397
No. of reflections ($>3\sigma$)	1170
Refined thickness (Å)	416
$R1(>3\sigma)$ (%)	12.58
$wR1(>3\sigma)$ (%)	16.04
$R1(all)$ (%)	19.70
$wR1(>3\sigma)$ (%)	17.07
Goodness of fit	7.45

Table S2. Selected crystallographic parameters from structure solution (SIR2014) and dynamical refinement (JAAN2006) of kangjinlaite.

Crystallographic information	
Cell content	$\text{P}_{10.4}\text{Si}_{29.6}\text{Ti}_{44}$
Space group	$I4/mmm$
a (Å)	9.4(2)
c (Å)	13.5(3)
Volume (Å ³)	1190(40)
Structure solution parameters	
Data resolution (Å)	0.9
No. of sampled reflections	2101
No. of independent reflections	283
Independent reflections coverage (%)	100
Global thermal factor U_{iso} (Å ²)	-0.026
$R_{\text{int}}(F)$ (%)	25.60
$R_{\text{sir}}(F)$ (%)	34.33
Dynamical structure refinement parameters	
No. of zones used for refinement	111
No. of reflections (all)	4836
No. of reflections ($>3\sigma$)	3829
Refined thickness (Å)	651
$R1(>3\sigma)$ (%)	14.94
$wR1(>3\sigma)$ (%)	17.08
$R1(\text{all})$ (%)	21.77
$wR1(>3\sigma)$ (%)	17.60
Goodness of fit	4.10

Table S3. X-ray powder diffraction data obtained by simulation for wenjiite

<i>I</i> /meas	<i>h</i>	<i>k</i>	<i>l</i>	2 θ (°)	<i>d</i> (Å)
0.17	1	0	0	14.00	6.32
5.82	1	1	0	24.37	3.65
3.94	2	0	0	28.21	3.16
4.86	1	1	1	30.10	2.97
10.52	0	0	2	35.24	2.55
31.33	2	1	0	37.61	2.39
16.77	1	0	2	38.09	2.36
100.00	2	1	1	41.73	2.16
38.90	3	0	0	42.88	2.11
80.22	1	1	2	43.31	2.09
2.48	2	0	2	45.73	1.98
2.33	2	2	0	49.93	1.83
1.45	3	1	0	52.12	1.75
1.60	2	1	2	52.49	1.74
4.71	2	2	1	53.28	1.72
4.97	3	1	1	55.38	1.66
1.16	3	0	2	56.66	1.62
3.18	4	0	0	58.34	1.58

Note: Bold – most intense reflections

Table S4. X-ray powder diffraction data obtained by simulation for kangjinlaite

<i>I</i> /meas	<i>h</i>	<i>k</i>	<i>l</i>	2 θ (°)	<i>d</i> (Å)
0.79	1	0	1	11.46	7.71
1.70	0	0	2	13.11	6.75
6.10	1	1	0	13.31	6.65
0.54	1	1	2	18.72	4.74
0.47	2	0	0	18.87	4.70
0.09	1	0	3	21.88	4.06
0.04	2	1	1	22.13	4.01
0.36	2	0	2	23.04	3.86
0.02	0	0	4	26.39	3.38
3.52	2	2	0	26.80	3.32
1.13	2	1	3	29.04	3.07
7.01	3	0	1	29.24	3.05
0.04	1	1	4	29.66	3.01
2.17	2	2	2	29.94	2.98
0.15	3	1	0	30.04	2.97
4.99	2	0	4	32.64	2.74
0.94	3	1	2	32.90	2.72
4.42	1	0	5	34.54	2.60
4.27	3	0	3	34.86	2.57
1.81	3	2	1	35.03	2.56
2.65	2	2	4	37.97	2.37
35.35	4	0	0	38.27	2.35
84.51	2	1	5	39.64	2.27
100.00	3	2	3	39.93	2.26
14.20	0	0	6	40.04	2.25
11.10	4	1	1	40.08	2.25
33.44	3	1	4	40.40	2.23
39.93	4	0	2	40.62	2.22
63.48	3	3	0	40.69	2.22
10.55	1	1	6	42.38	2.13
19.64	3	3	2	42.93	2.11
1.50	4	2	0	43.00	2.10
36.68	3	0	5	44.25	2.05
5.44	4	1	3	44.51	2.03
13.22	2	0	6	44.61	2.03
3.69	4	2	2	45.14	2.01
7.97	4	0	4	47.08	1.93
0.70	1	0	7	48.13	1.89
2.41	3	2	5	48.50	1.88

0.51	2	2	6	48.84	1.86
2.85	5	0	1	48.87	1.86
0.08	4	3	1	48.87	1.86
2.10	3	3	4	49.15	1.85
0.12	5	1	0	49.40	1.84
2.30	3	1	6	50.86	1.79
1.51	4	2	4	51.16	1.78
0.55	5	1	2	51.34	1.78
2.19	2	1	7	52.14	1.75
3.63	4	1	5	52.49	1.74
13.53	5	0	3	52.73	1.74
5.65	4	3	3	52.73	1.74
0.45	5	2	1	52.84	1.73
0.02	0	0	8	54.32	1.69
5.30	4	4	0	55.23	1.66
0.04	3	0	7	55.94	1.64
0.98	1	1	8	56.19	1.64
0.98	5	2	3	56.50	1.63
1.15	4	0	6	56.59	1.63
0.12	5	1	4	56.86	1.62
8.43	4	4	2	57.03	1.61
0.00	5	3	0	57.09	1.61
1.09	2	0	8	58.03	1.59
3.55	3	3	6	58.41	1.58
1.60	5	3	2	58.85	1.57
15.83	6	0	0	58.90	1.57
1.92	3	2	7	59.58	1.55
1.74	4	3	5	59.90	1.54
3.72	5	0	5	59.90	1.54

Note: Bold – most intense reflections

Table S5. Coordinates and equivalent displacement parameters (U_{iso} Å²) of atoms in wenjiite

Label	Williams ¹	x/a	y/b	z/c	U_{iso}	occupancy	multiplicity
Ti1	Ti ^{4d}	$\frac{2}{3}$	$\frac{1}{3}$	0	0.0053(8)	1	4
Ti2	Ti ^{6g}	0.7614(3)	0	0.25	0.0060(7)	1	6
Si1	Si	0.5981(6)	0.5981(6)	0.25	0.0071(9)	0.77	6
P1	—	0.5981(6)	0.5981(6)	0.25	0.0071(9)	0.23	6
Si2	Z	0	0	0	0.020(4)	0.385	2
P2	—	0	0	0	0.020(4)	0.115	2

Note: 1. Site designation from Williams et al. (2000a,b)

Table S6. Coordinates and equivalent displacement parameters (U_{iso} Å²) of atoms in kangjinlaite

Label	x/a	y/b	z/c	U_{iso}	occupancy	multiplicity
Ti1	0.1811(3)	0.1811(3)	0	0.005	1	8
Ti2	0.5	0.1654(3)	0.10097(16)	0.005	1	16
Ti3	0.2509(3)	0	0.18651(15)	0.005	1	16
Ti4	0.5	0.5	0.1661(3)	0.005	1	4
Si1	0.3720(4)	0.3720(4)	0	0.005	0.74	8
P1	0.3720(4)	0.3720(4)	0	0.005	0.26	8
Si2	0	0	0.1030(5)	0.005	0.74	4
P2	0	0	0.1030(5)	0.005	0.26	4
Si3	0.2937(3)	0.2937(3)	0.1742(2)	0.005	0.74	16
P3	0.2937(3)	0.2937(3)	0.1742(2)	0.005	0.26	16
Si4	0.3595(6)	0	0	0.005	0.74	8
P4	0.3595(6)	0	0	0.005	0.26	8
Si5	0.5	0	0.25	0.005	0.74	4
P5	0.5	0	0.25	0.005	0.26	4

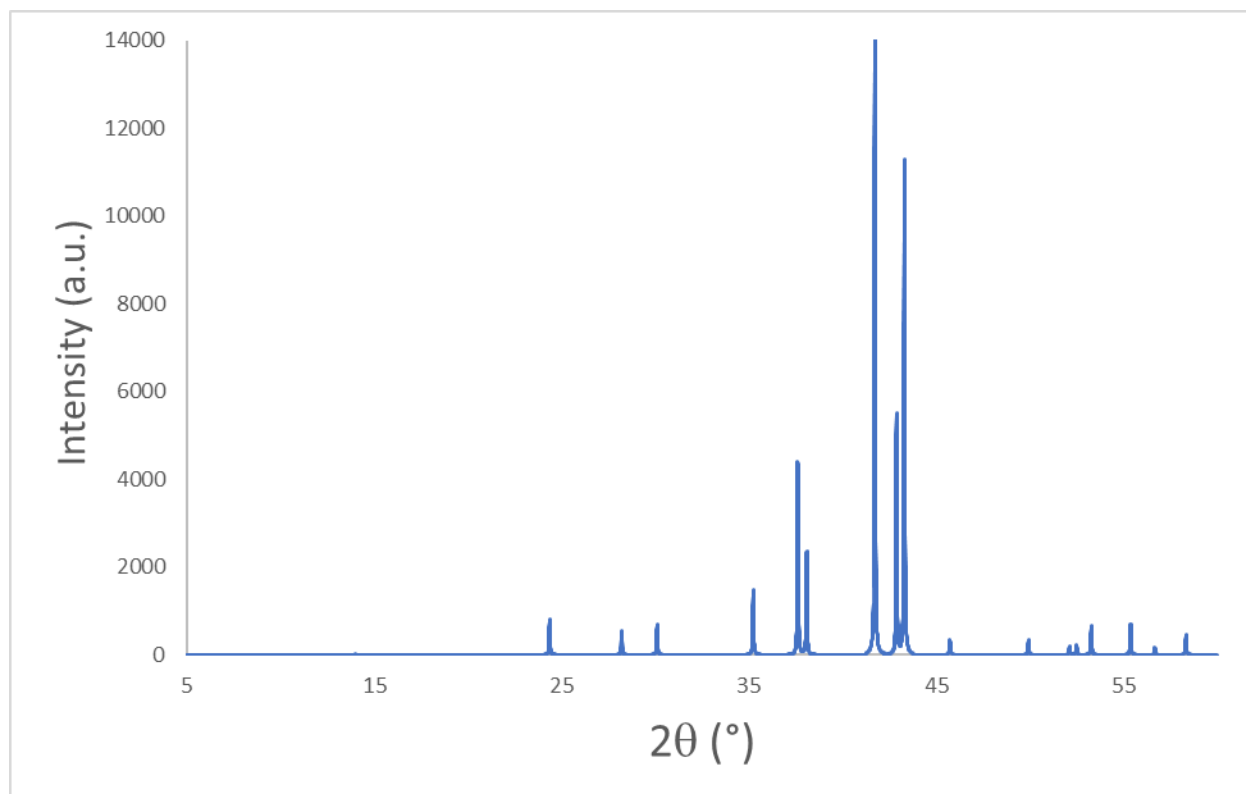


Figure S1. Simulated X-ray powder pattern of wenjiite with CuK α_1 radiation

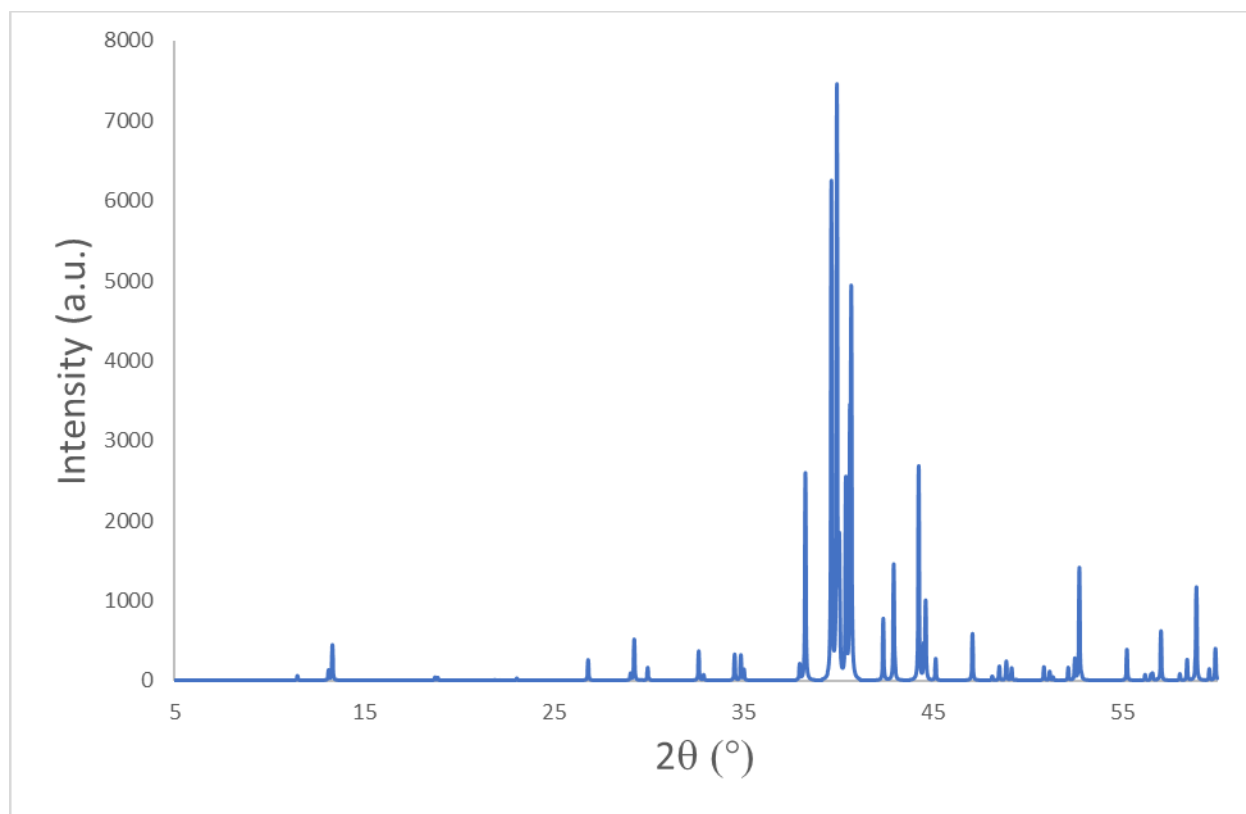


Figure S2. Simulated X-ray powder pattern of kangjinlaite with $\text{CuK}\alpha_1$ radiation

H																		He
Li	Be												B	C	N	O	F	Ne
Na	Mg												Al	Si	P	S	Cl	Ar
K	Ca	Sc	Ti	V	Cr	Mn	Fe	Co	Ni	Cu	Zn	Ga	Ge	As	Se	Br	Kr	
Rb	Sr	Y	Zr	Nb	Mo	Tc	Ru	Rh	Pd	Ag	Cd	In	Sn	Sb	Te	I	Xe	
Cs	Ba	La	Hf	Ta	W	Re	Os	Ir	Pt	Au	Hg	Tl	Pb	Bi	Po	At	Rn	
Fr	Ra	Ac																
			Ce	Pr	Nd	Pm	Sm	Eu	Gd	Tb	Dy	Ho	Er	Tm	Yb	Lu		
			Th	Pa	U													
	Reported as an occupant at the Ho site																	
	Reported as an occupant at the Ge site																	
	Reported as an occupant at both sites																	
	Reported only in kangjinlaite																	
	Reported only in Eu ₁₁ As ₁₀																	

Figure S3. The Periodic Table showing the 38 elements reported in compounds isostructural with Ho₁₁Ge₁₀, including kangjinlaite.

Appendix II

References for Figure 10

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